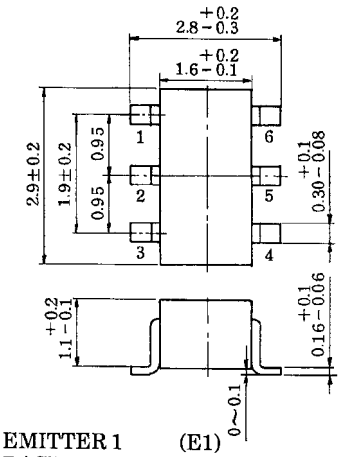
TOSHIBA Transistor Silicon Npn Epitaxial Type (PCT Process)

RN1610,RN1611

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

- Including two devices in SM6 (super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN2610, RN2611

Unit: mm

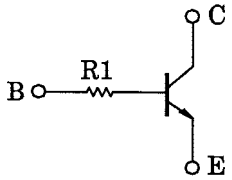


1. EMITTER 1 (E1)
2. BASE 1 (B1)
3. COLLECTOR 2 (C2)
4. EMITTER 2 (E2)
5. BASE 2 (B2)
6. COLLECTOR 1 (C1)

JEDEC	—
EIAJ	—
TOSHIBA	2-3N1A

Weight: 0.015g

Equivalent Circuit

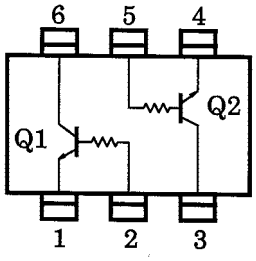


Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characterisstic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector power dissipation	P_C*	300	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	−55~150	°C

* Total rating

Equivalent Circuit (Top View)



Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	—	V_{CB} = 50V, I_E = 0	—	—	100	nA
Emitter cut-off current		I_{EBO}	—	V_{EB} = 50V, I_C = 0	—	—	100	nA
DC current gain		h_{FE}	—	V_{CE} = 50V, I_C = 1mA	120	—	700	—
Collector-emitter saturation voltage		$V_{CE\ (sat)}$	—	I_C = 5mA, I_B = 0.25mA	—	0.1	0.3	V
Translation frequency		f_T	—	V_{CE} = 10V, I_C = 5mA	—	250	—	MHz
Collector output capacitance		C_{ob}	—	V_{CB} = 10V, I_E = 0, f = 1MHz	—	3	6	pF
Input resistor	RN1610	R1	—	—	3.29	4.7	6.11	kΩ
	RN1611				7	10	13	

(Q1, Q2 Common)